

Features

- High Speed Switching Time
- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings @ 25°C Unless Otherwise Specified

- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 250°C/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Base Current	I_B	-0.4	A
Collector Power Dissipation	P_C	500 1000 ^(Note2)	mW

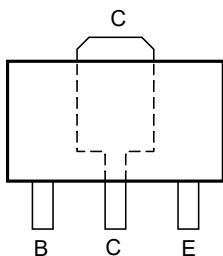
Classification Of h_{FE}

Rank	O	Y
Range	70-140	120-240
Marking	NO	NY

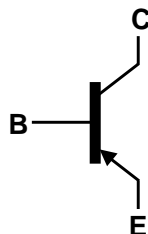
Note 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Note 2. Mounted on ceramic substrate (250mm² x 0.8t)

Pin Configuration - Top View

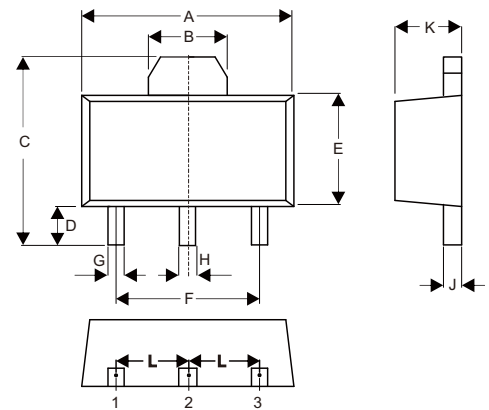


Internal Structure



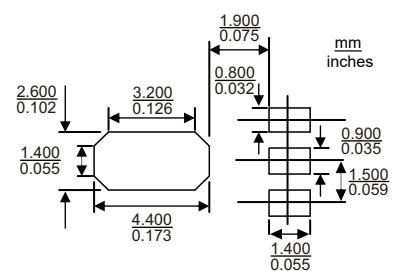
PNP Silicon Epitaxial Transistors

SOT-89



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.169	0.185	4.30	4.70	
B	0.061		1.55		TYP.
C	0.154	0.171	3.91	4.35	
D	0.031	0.047	0.80	1.20	
E	0.089	0.104	2.25	2.65	
F	0.118		3.00		TYP.
G	0.013	0.020	0.33	0.52	
H	0.015	0.021	0.38	0.53	
J	0.014	0.017	0.35	0.44	
K	0.055	0.063	1.40	1.60	
L	0.059		1.50		TYP.

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50			V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-50			V	$I_C = -10mA, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A, I_C = 0$
Collector-Base Cutoff Current	I_{CBO}			-0.1	μA	$V_{CB} = -50V, I_E = 0$
Emitter-Base Cutoff Current	I_{EBO}			-0.1	μA	$V_{EB} = -5V, I_C = 0$
DC Current Gain	h_{FE1}	70		240		$V_{CE} = -2Vdc, I_C = -0.5A$
	h_{FE2}	20				$V_{CE} = -2Vdc, I_C = -2A$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C = -1A, I_B = -50mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.2	V	$I_C = -1A, I_B = -50mA$
Transition Frequency	f_T	100	120		MHz	$V_{CE} = -2V, I_C = -0.5A$
Collector Output Capacitance	C_{ob}		40		pF	$V_{CB} = -10V, I_E = 0, f = 1.0MHz$

Curve Characteristics

Fig. 1 - Static Characteristics

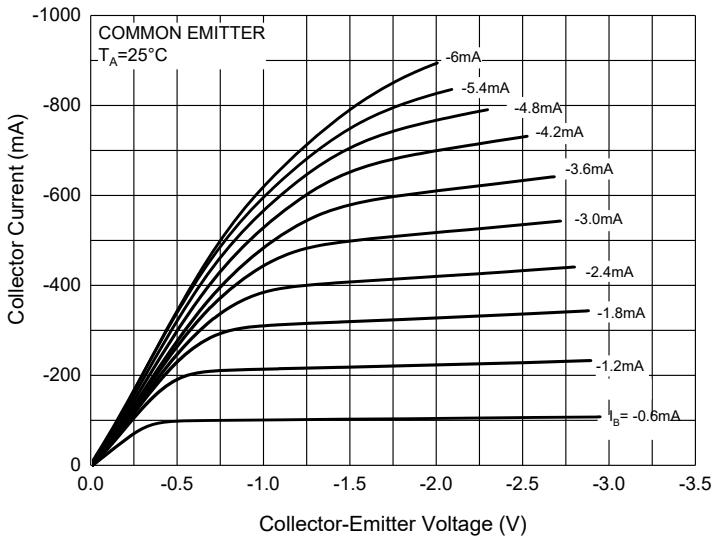


Fig. 2 - DC Current Gain Characteristics

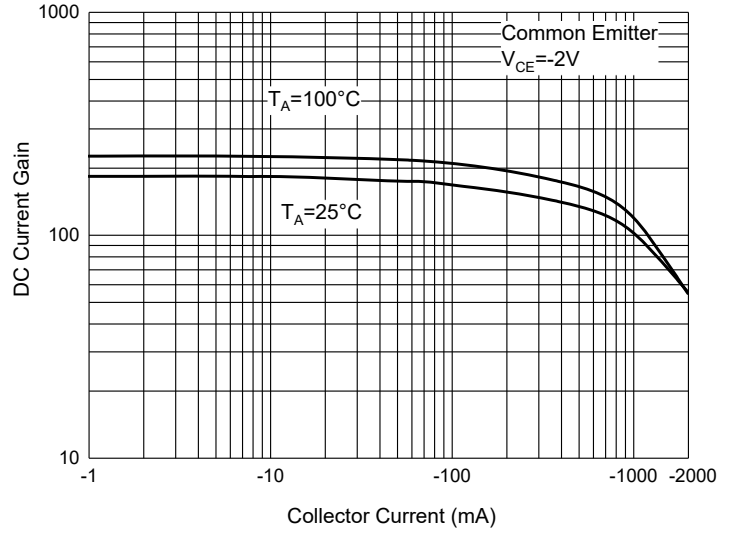


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

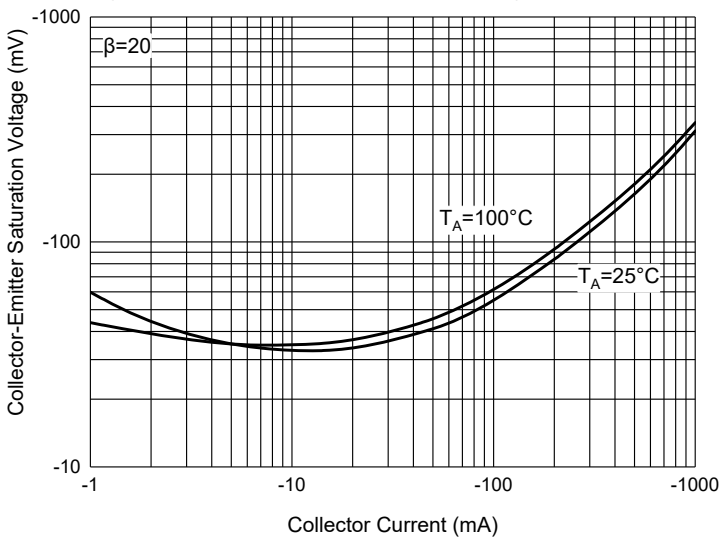


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

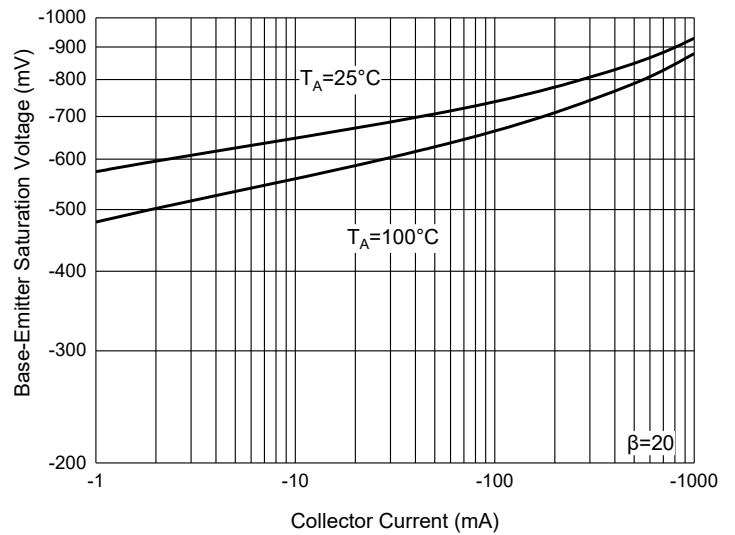


Fig. 5 - Base-Emitter Voltage Characteristics

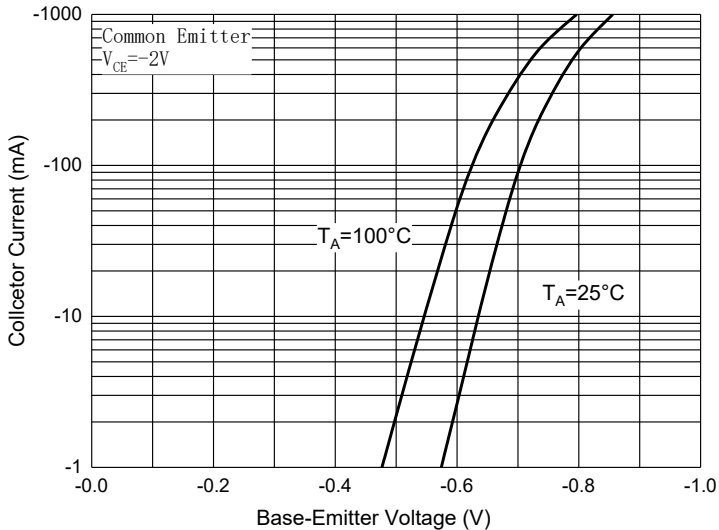


Fig. 6 - Power Derating Curve

